



#### 60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
60V	$12m\Omega @ V_{GS} = 10V$	80A
	$18m\Omega @ V_{GS} = 4.5V$	70A

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AECQ101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC/DC Converters

## **Features**

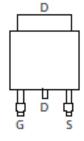
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures more Reliable and Robust End Application
- Low On-Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

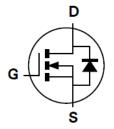
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.33 grams (Approximate)







Pin Out Top View



**Equivalent Circuit** 

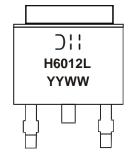
# **Ordering Information** (Note 5)

Part Number	Case	Packaging
DMNH6012LK3Q-13	TO252 (DPAK)	2500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



Dil =Manufacturer's Marking
H6012L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 16 = 2016)
WW = Week Code (01 to 53)



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	60	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 8), V <sub>GS</sub> = 10V	$T_C = +25$ °C $T_C = +100$ °C	I <sub>D</sub>	80 60	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	120	Α
Maximum Continuous Body Diode Forward Current (Note 8)		I <sub>S</sub>	80	Α
Avalanche Current, L = 0.1mH (Note 9)		I <sub>AS</sub>	45	Α
Avalanche Energy, L = 0.1mH (Note 9)		Eas	100	mJ

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

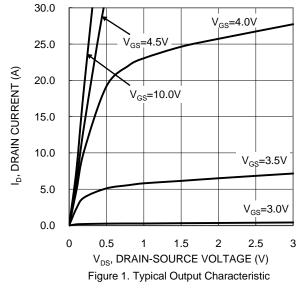
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)		P <sub>D</sub>	2.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	74	°C/W
Total Power Dissipation (Note 7)		P <sub>D</sub>	3.8	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	40	°C/W
Thermal Resistance, Junction to Case (Note 8)		$R_{\theta JC}$	1.2	C/VV
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage		60		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current, T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 60V$ , $V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D	_	8	12	mΩ	$V_{GS} = 10V, I_D = 25A$	
Static Dialit-Source Off-Resistance	R <sub>DS(ON)</sub>	_	10	18	11122	$V_{GS} = 4.5V, I_D = 25A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.7A$	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	C <sub>iss</sub>	_	1926	_	pF	.,	
Output Capacitance	Coss	1	330	_	pF	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	112	_	pF	1 – 11011 12	
Gate Resistance	Rg	_	2.0	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	1	16.3	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	35.2	_	nC	V <sub>DS</sub> = 30V. I <sub>D</sub> = 25A	
Gate-Source Charge	Q <sub>gs</sub>	_	7.6	_	nC	VDS = 30V, ID = 25A	
Gate-Drain Charge	$Q_{gd}$	_	6.9	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.4	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	11.9	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_g = 3\Omega, I_D = 25A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	16.5	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	5	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	28	_	ns	I <sub>F</sub> = 25A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge		_	23	_	nC	$I_F = 25A$ , $di/dt = 100A/\mu s$	

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 8. Thermal resistance from junction to soldering point (on the exposed drain pad).
- I. As and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.





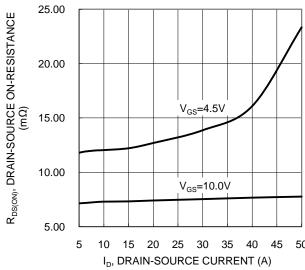


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

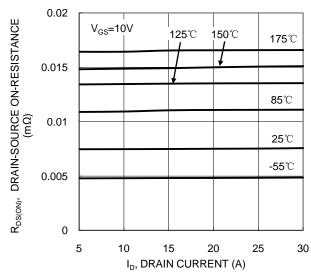
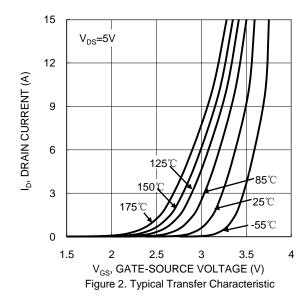
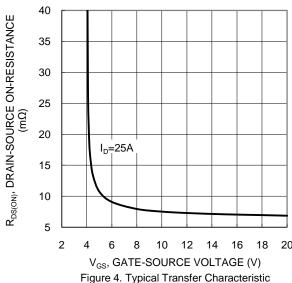


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





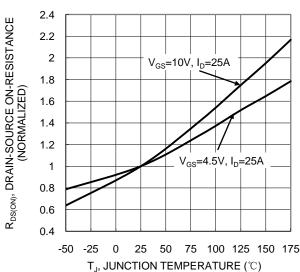


Figure 6. On-Resistance Variation with Temperature



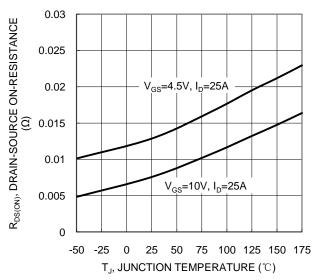
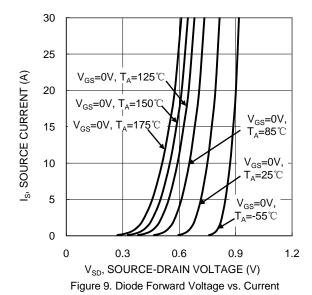


Figure 7. On-Resistance Variation with Temperature



10000 f=1MHz C<sub>T</sub>, JUNCTION CAPACITANCE (pF)  $C_{\text{iss}}$ 1000  $C_{\rm oss}$ 100  $C_{rss}$ 10 0 5 10 15 20 25 30 35 40 45 50 55 60 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure: 11. Typical Junction Capacitance

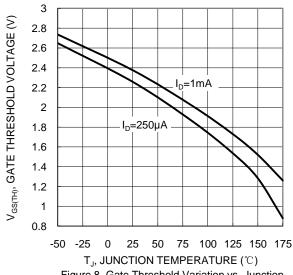
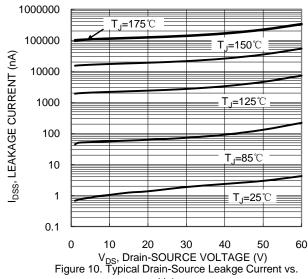


Figure 8. Gate Threshold Variation vs. Junction Temperature



Voltage

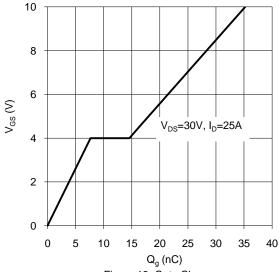
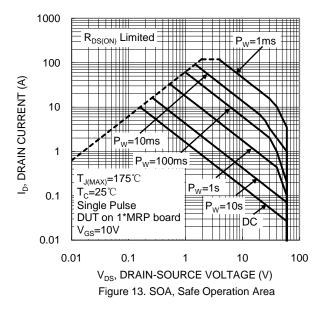
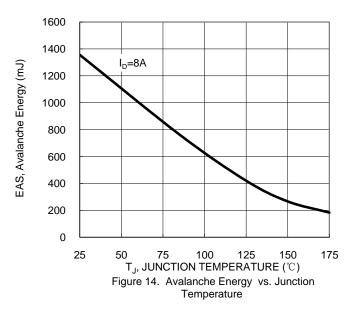


Figure 12. Gate Charge







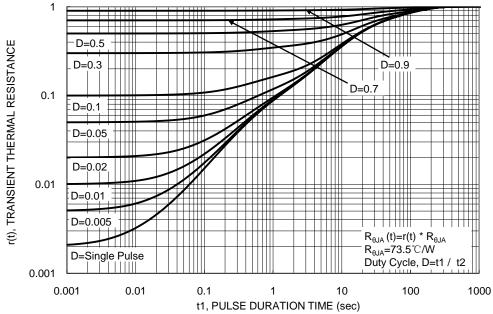


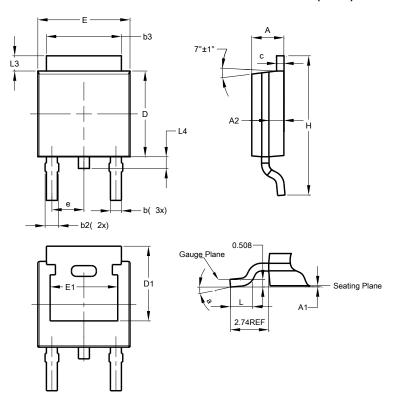
Figure 15. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## TO252 (DPAK)



TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
<b>A1</b>	0.00	0.13	0.08		
<b>A2</b>	0.97	1.17	1.07		
þ	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
O	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
H	9.40	10.41	9.91		
Г	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TO252 (DPAK)

Dimensions	Value (in mm)
С	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10 700



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